

AMENDMENTS TO THE SPECIFICATION

Amend the paragraph beginning at page 6, line 3 as follows:

(Currently Amended) The inventor, however, find uniquely that formation of an AlN single crystalline layer 2 instead of the conventional low-temperature buffer layer 100 on the sapphire substrate 1, as shown in FIG. 1(b), causes the sapphire substrate 1 to be warped so as to be concave toward the nitride compound semiconductor 2, contrary to the prior-art commonsense. Based on these results, the inventor consider that when the ~~AlN~~ AlN single crystalline layer 2 is formed on the sapphire substrate 1 and a layer having a lattice constant larger than the AlN single crystalline layer 2 is formed on the AlN single crystalline layer 2, stresses would be modified and the warp would disappear.

Amend the paragraph beginning at page 8, line 9 as follows:

(Currently Amended) The element of FIG. 2 comprises a sapphire substrate 1, a first single crystalline layer 2 of AlN formed on a c-surface of the sapphire substrate and a second single crystalline layer 3. The first single crystalline layer 2 is doped with carbon having a concentration of equal to or more than $3 \times 10^{18} \text{ cm}^{-3}$ and equal to or less than $1 \times 10^{20} \text{ cm}^{-3}$, and has a thickness of equal to or more than 10 nm and equal to or less than 50 nm. The second single crystalline layer 3 is made of $\text{Al}_{0.9}\text{Ga}_{0.1}\text{N}$ and has a thickness of 1.5 μm . A single crystalline AlN protective layer 4 is formed directly on the second single crystalline layer 3. The single crystalline ~~AlN~~ AlN protective layer 4 prevents Ga atoms from evaporating from said second single crystalline layer 3 in crystal growth to thereby protect the second single crystalline layer 3, and the single crystalline ~~AlN~~ AlN protective layer has a thickness of equal to or more than 1 nm and equal to or less than 10 nm.